


**45V MATCHED PAIR PNP SMALL SIGNAL TRANSISTOR IN SOT363**
**Features**

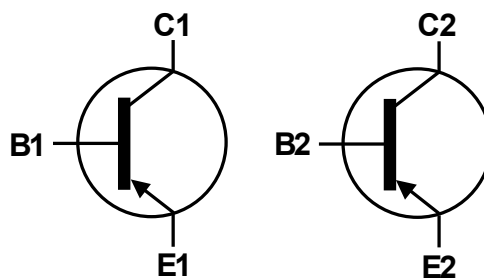
- $BV_{CEO} > -45V$
- $I_C = -100mA$  High Collector Current
- Pair of PNP Transistors That Are Intrinsically Matched (Note 1)
- 10% Matching on Current Gain ( $h_{FE}$ )
- 2mV Matching on Base-Emitter Voltage ( $V_{BE}$ )
- Fully Internally Isolated in a Small Surface Mount Package
- **Totally Lead-Free & Fully RoHS compliant (Notes 2 & 3)**
- **Halogen and Antimony Free. "Green" Device (Note 4)**
- **Qualified to AEC-Q101 for High Reliability**

**Mechanical Data**

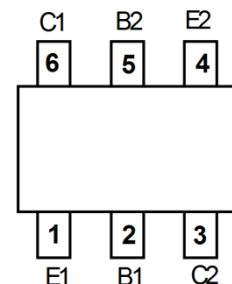
- Case: SOT363
- Case Material: Molded Plastic, "Green" Molding Compound  
UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish — Matte Tin Finish. Solderable per  
MIL-STD-202, Method 208 
- Weight: 0.006 grams (approximate)



Top View



Device Symbol


 Top View  
Pin-Out

**Ordering Information** (Note 5)

Product	Compliance	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
BCM857BS-7-F	AEC-Q101	M3W	7	8	3,000

- Notes:
1. Intrinsically matched pair as this is built with adjacent die from the same wafer.
  2. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
  3. See [http://www.diodes.com/quality/lead\\_free.html](http://www.diodes.com/quality/lead_free.html) for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
  4. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
  5. For packaging details, go to our website at <http://www.diodes.com/products/packages.html>.

**Marking Information**


M3W = Product Type Marking Code  
 YM = Date Code Marking  
 Y = Year (ex: B = 2014)  
 M = Month (ex: 9 = September)

**Date Code Key**

Year	2014	2015	2016	2017	2018	2019	2020	2021
Code	B	C	D	E	F	G	H	I

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

**Absolute Maximum Ratings** (@T<sub>A</sub> = +25°C unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V <sub>CBO</sub>	-50	V
Collector-Emitter Voltage	V <sub>CEO</sub>	-45	V
Emitter-Base Voltage	V <sub>EBO</sub>	-5.0	V
Collector Current	I <sub>C</sub>	-100	mA
Peak Collector Current	I <sub>CM</sub>	-200	mA
Peak Base Current	I <sub>BM</sub>	-200	mA

**Thermal Characteristics** (@T<sub>A</sub> = +25°C unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 6) Total Device	P <sub>D</sub>	200	mW
Thermal Resistance, Junction to Ambient Air (Note 6)	R <sub>θJA</sub>	625	°C/W
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-65 to +150	°C

**ESD Ratings** (Note 7)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	400	V	C

**Electrical Characteristics** (@T<sub>A</sub> = +25°C unless otherwise specified.)

Characteristic (Note 8)	Symbol	Min	Typ	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV <sub>CBO</sub>	-50	—	—	V	I <sub>C</sub> = 100μA, I <sub>B</sub> = 0
Collector-Emitter Breakdown Voltage	BV <sub>CEO</sub>	-45	—	—	V	I <sub>C</sub> = 10mA, I <sub>B</sub> = 0
Emitter-Base Breakdown Voltage	BV <sub>EBO</sub>	-5	—	—	V	I <sub>E</sub> = 100μA, I <sub>C</sub> = 0
DC Current Gain	h <sub>FE</sub>	220	—	475	—	V <sub>CE</sub> = -5.0V, I <sub>C</sub> = -2.0mA
DC Current Gain matching (Note 9)	h <sub>FE1</sub> / h <sub>FE2</sub>	0.9	1	—	—	V <sub>CE</sub> = -5.0V, I <sub>C</sub> = -2.0mA
Collector-Emitter Saturation Voltage	V <sub>CE(sat)</sub>	—	—	-100 -400	mV	I <sub>C</sub> = -10mA, I <sub>B</sub> = -0.5mA I <sub>C</sub> = -100mA, I <sub>B</sub> = -5.0mA
Base-Emitter Saturation Voltage	V <sub>BE(sat)</sub>	—	-700	—	mV	I <sub>C</sub> = -10mA, I <sub>B</sub> = -0.5mA
Base-Emitter Voltage	V <sub>BE(on)</sub>	-580	-665	-750	mV	V <sub>CE</sub> = -5.0V, I <sub>C</sub> = -2.0mA
Base-Emitter Voltage matching (Note 10)	V <sub>BE1(on)</sub> - V <sub>BE2(on)</sub>	—	—	2	mV	V <sub>CE</sub> = -5.0V, I <sub>C</sub> = -2.0mA
Base-Emitter Voltage	V <sub>BE(on)</sub>	-580	-665	-750	mV	V <sub>CE</sub> = -5.0V, I <sub>C</sub> = -2.0mA
Collector-Cutoff Current	I <sub>CBO</sub>	—	—	-15 -4.0	nA μA	V <sub>CB</sub> = -30V V <sub>CB</sub> = -30V, T <sub>A</sub> = +150°C
Emitter Cutoff Current	I <sub>EBO</sub>	—	—	-100	nA	V <sub>EB</sub> = -5.0V, I <sub>C</sub> = 0
Gain Bandwidth Product	f <sub>T</sub>	100	—	—	MHz	V <sub>CE</sub> = -5.0V, I <sub>C</sub> = -10mA, f = 100MHz
Collector-Base Capacitance	C <sub>CBO</sub>	—	2	3	pF	V <sub>CB</sub> = -10V, f = 1.0MHz
Emitter-Base Capacitance	C <sub>EBO</sub>	—	11	—	pF	V <sub>EB</sub> = -0.5V, f = 1.0MHz

- Notes:
6. For a device mounted on minimum recommended pad layout with 1oz copper that is on a single-sided 1.6mm FR4 PCB; the device is measured under still air conditions whilst operating in a steady-state.
  7. Refer to JEDEC specification JESD22-A114 and JESD22-A115.
  8. Short duration pulse test used to minimize self-heating effect.
  9. The smaller of the two values is taken as the numerator.
  10. The smaller of the two values is subtracted from the larger value.

**Typical Electrical Characteristics** (@ $T_A = +25^\circ\text{C}$  unless otherwise specified.)

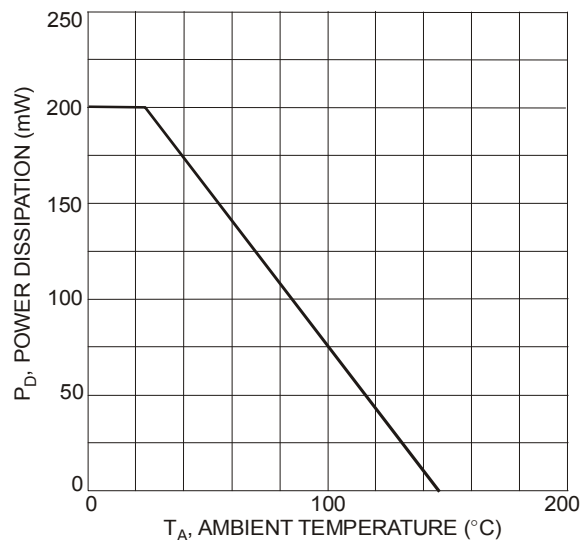


Fig. 1 Power Dissipation vs. Ambient Temperature

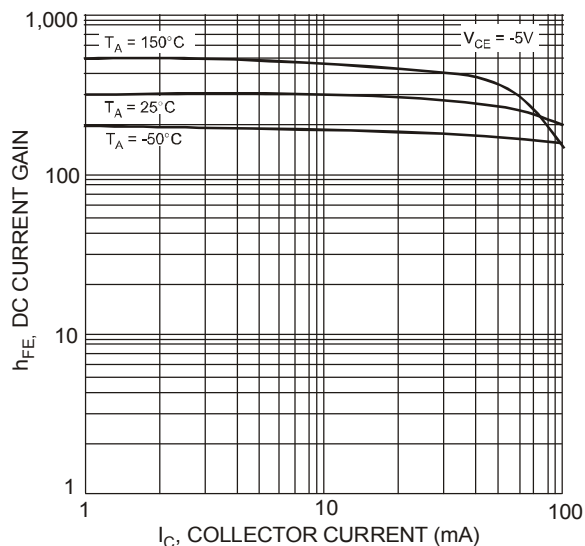


Fig. 2 Typical DC Current Gain vs. Collector Current

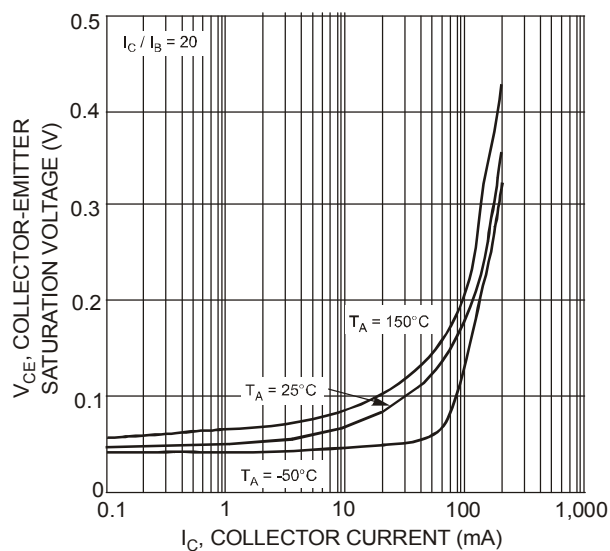


Fig. 3 Typical Collector-Emitter Saturation Voltage vs. Collector Current

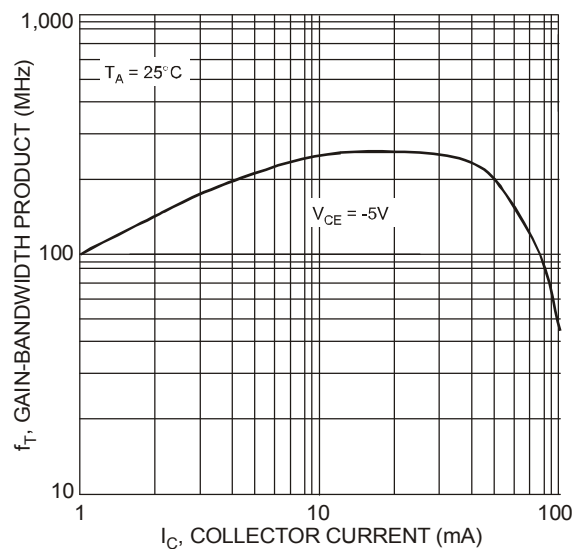
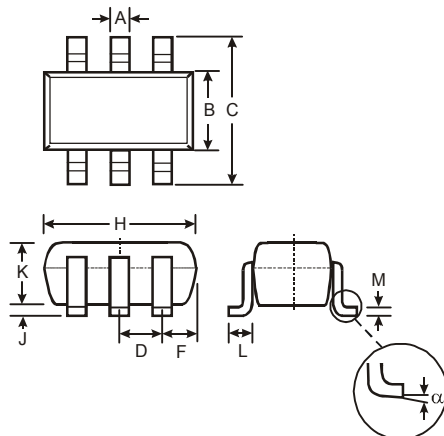


Fig. 4 Typical Gain-Bandwidth Product vs. Collector Current

## Package Outline Dimensions

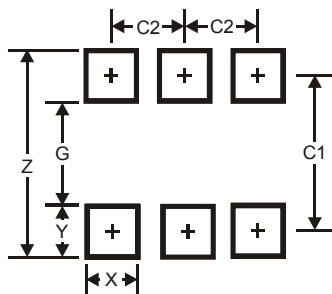
Please see AP02002 at <http://www.diodes.com/datasheets/ap02002.pdf> for latest version.



SOT363			
Dim	Min	Max	Typ
A	0.10	0.30	0.25
B	1.15	1.35	1.30
C	2.00	2.20	2.10
D	0.65 Typ		
F	0.40	0.45	0.425
H	1.80	2.20	2.15
J	0	0.10	0.05
K	0.90	1.00	1.00
L	0.25	0.40	0.30
M	0.10	0.22	0.11
$\alpha$	0°	8°	-
All Dimensions in mm			

## Suggested Pad Layout

Please see AP02001 at <http://www.diodes.com/datasheets/ap02001.pdf> for the latest version.



Dimensions	Value (in mm)
Z	2.5
G	1.3
X	0.42
Y	0.6
C1	1.9
C2	0.65

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